Guangdong Yuejing High Technology CO.,LTD.

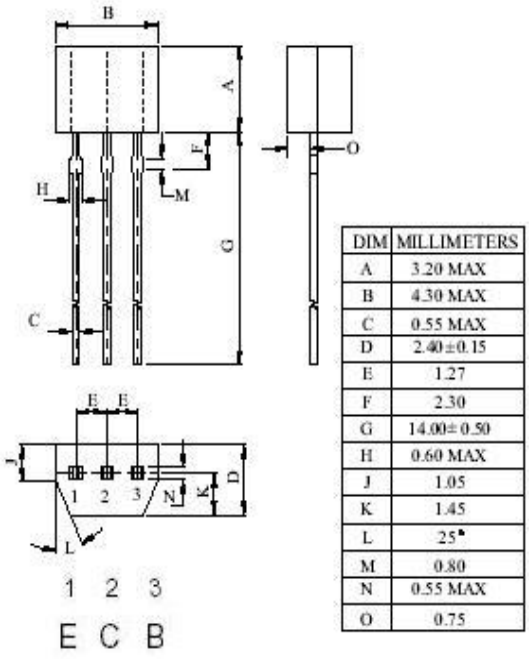
C4115S

NPN Transistors

—NPN Silicon—

■■ **APPLICATION：** Switching application,Amplifier application

TO-92S



DIM	MILLIMETERS
A	3.20 MAX
B	4.30 MAX
C	0.55 MAX
D	2.40±0.15
E	1.27
F	2.30
G	14.00±0.50
H	0.60 MAX
J	1.05
K	1.45
L	25°
M	0.80
N	0.55 MAX
O	0.75

■■ **MAXIMUM RATINGS**（Ta=25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	Ic	3	A
Collector current	Icp	5	A
Collector Power Dissipation	Pc	0.3	W
Junction Temperature	Tj	150	℃
Storage Temperature Range	Tstg	-55~150	℃

■■ **ELECTRICAL CHARACTERISTICS**（Ta=25℃，RG=10KΩ）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collectoe-Base Breakdown Voltage	BVcbo	40			V	Ic=50uA	Ie=0	
Collector-Emitter Breakdown Voltage	BVceo	20			V	Ic=1mA	Ib=0	
Emitter-Base Breakdown Voltage	BVebo	6			V	Ie=50uA	Ic=0	
Collector Cut-off Current	Icbo			0.1	uA	Vcb=30V	Ie=0	
Emitter Cut-off Current	Iebo			0.1	uA	Veb=5V	Ic=0	
Collector-Emitter Saturation Voltage	Vce(sat)		0.2	0.5	V	Ic=2A	Ib=0.1A	
DC Current Gain	h_{FE}	120		560	β	Vce=2V	Ic=0.1A	
Gain bandwidth product	f_T		290		MHz	Vce=2V	Ie=-0.5A	f=100MHz
Common Base Output Capacitance	Cob		25		pF	Vcb=10V	Ie=0	f=1MHz

■■ **h_{FE} Classification And Marking**

Print Mark	C4115S		
Classification	Q	R	S
h_{FE}	120~270	180~390	270~560